

C | D | T

# FUNDAMENTAL PROCESSES GOVERNING OPERATION AND AGEING IN STATE OF THE ART P-OLEDs

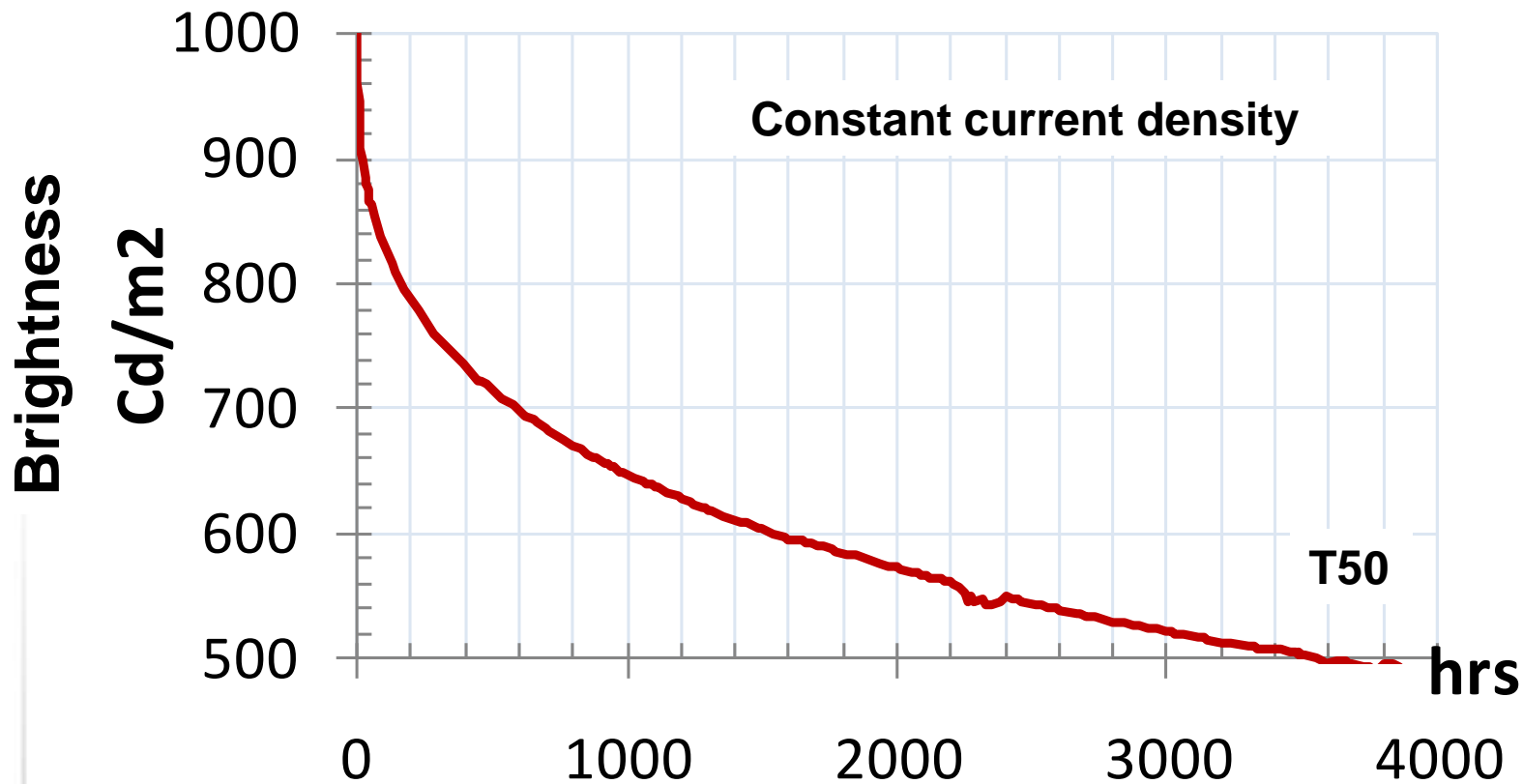
Matthew Roberts,<sup>1</sup> Michael Cass, Clare Foden, Simon King,  
Andrew Lee, Martina Pintani

*ECME 2009*

*Thursday September 10<sup>th</sup>*

# Lifetime testing of P-OLED devices

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**Key challenge for P-OLED – extending T50**

# Talk overview

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## Device fundamentals

- Basic device structure
- Model materials

## Degradation analysis

- Loss of carrier injection
- PL decay

## PL decay analysis

- What generates quench sites
- Properties of degraded material

# Talk overview

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- Basic device structure
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## Degradation analysis

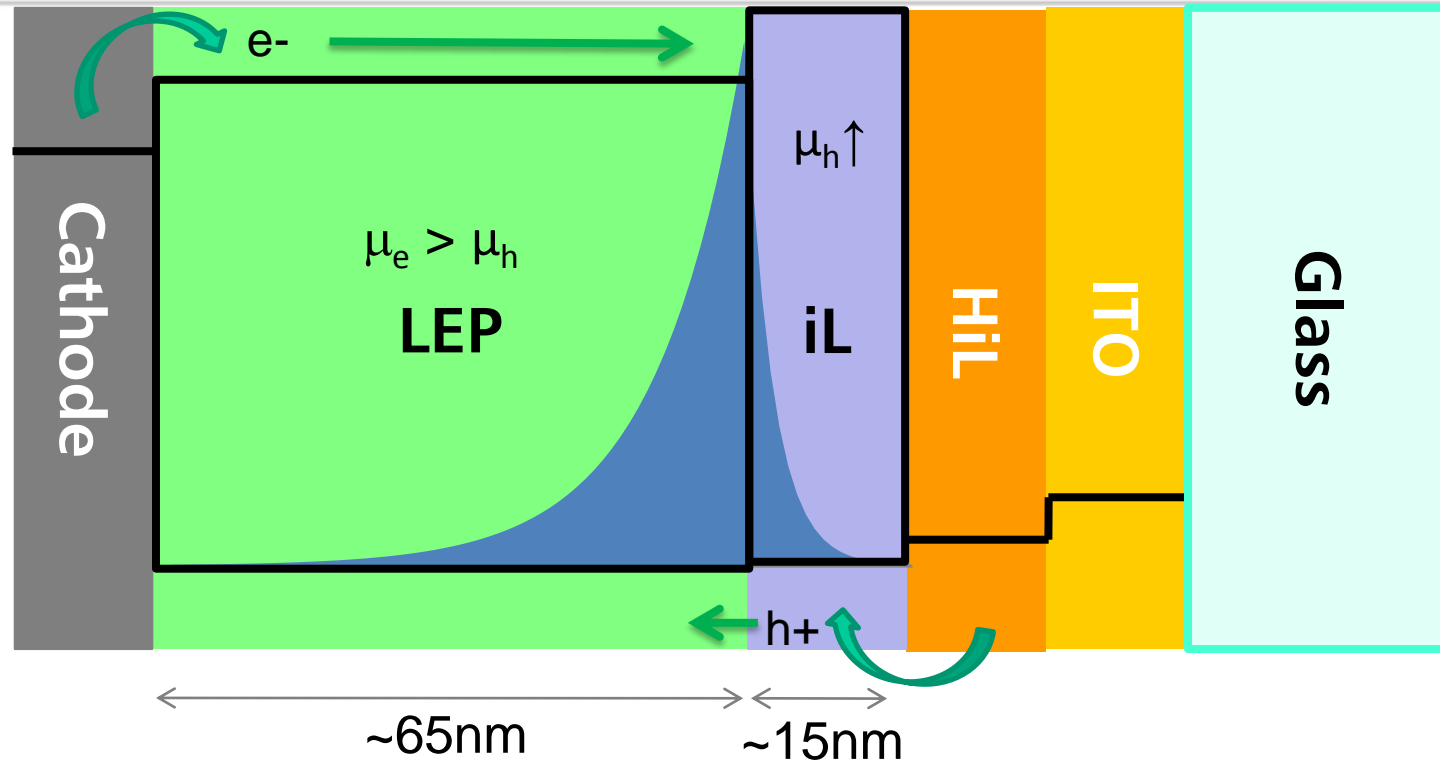
- Loss of carrier injection
- PL decay

## PL decay analysis

- What generates quench sites
- Properties of degraded material

# Device structure

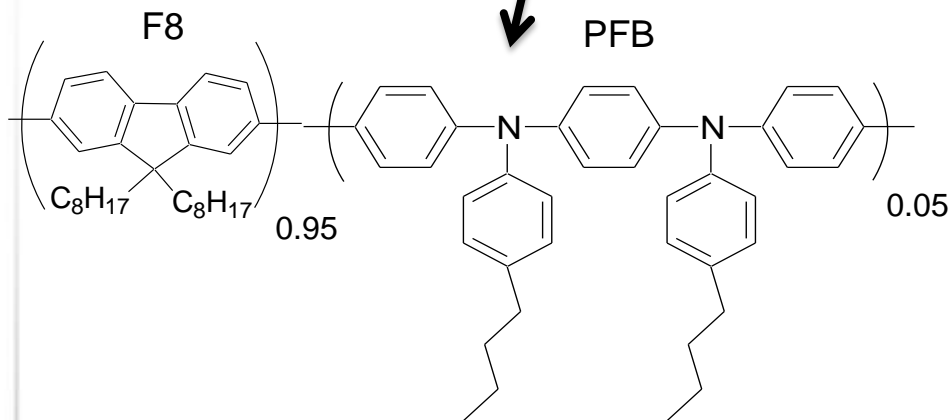
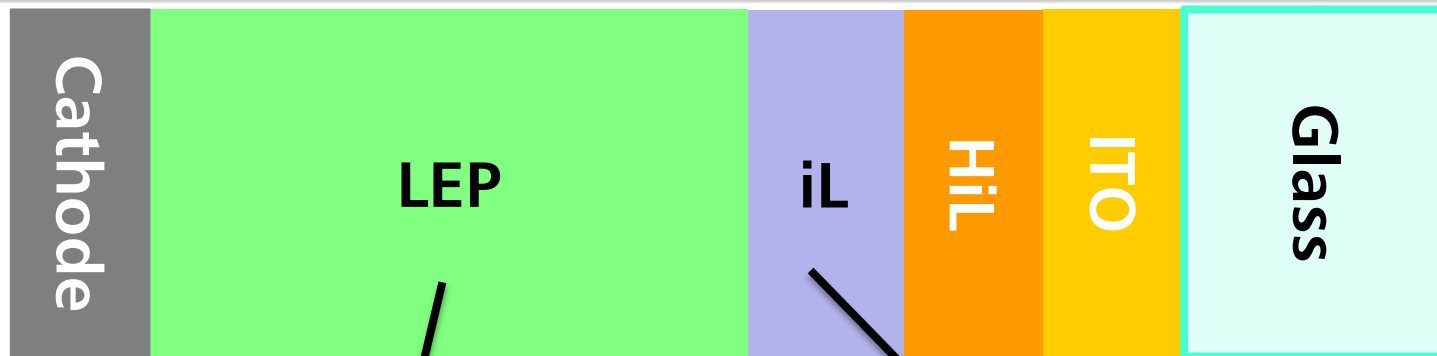
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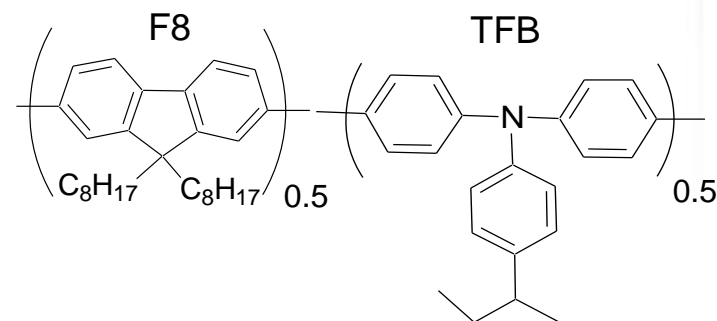
- LEP thickness and mobilities - Optimum RZ for outcoupling
- iL - hole injection, efficiency and lifetime
- HiL and ITO thicknesses – tuned for colour and outcoupling
- Electrodes / charge injection layers - thermally stable

# Model materials

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**Random copolymer**  
**F8:PFB 95:5**



**A-B copolymer**  
**F8:TFB 50:50**

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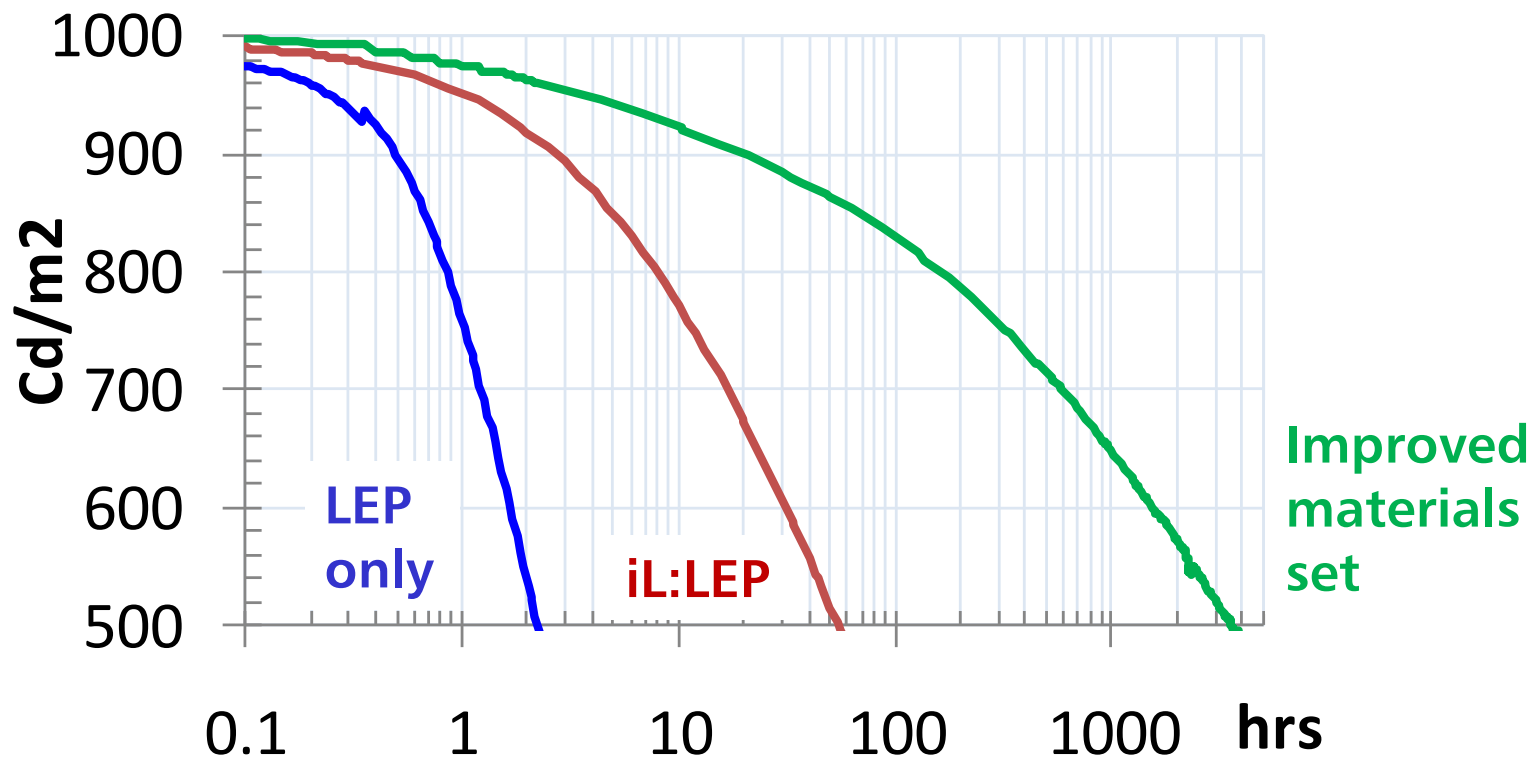
## PL decay analysis

- What generates quench sites
- Properties of degraded material

# Degradation analysis

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iL:LEP = Model materials



Degradation analysis of 3 systems spanning over 1000x in lifetime

# Case study 1

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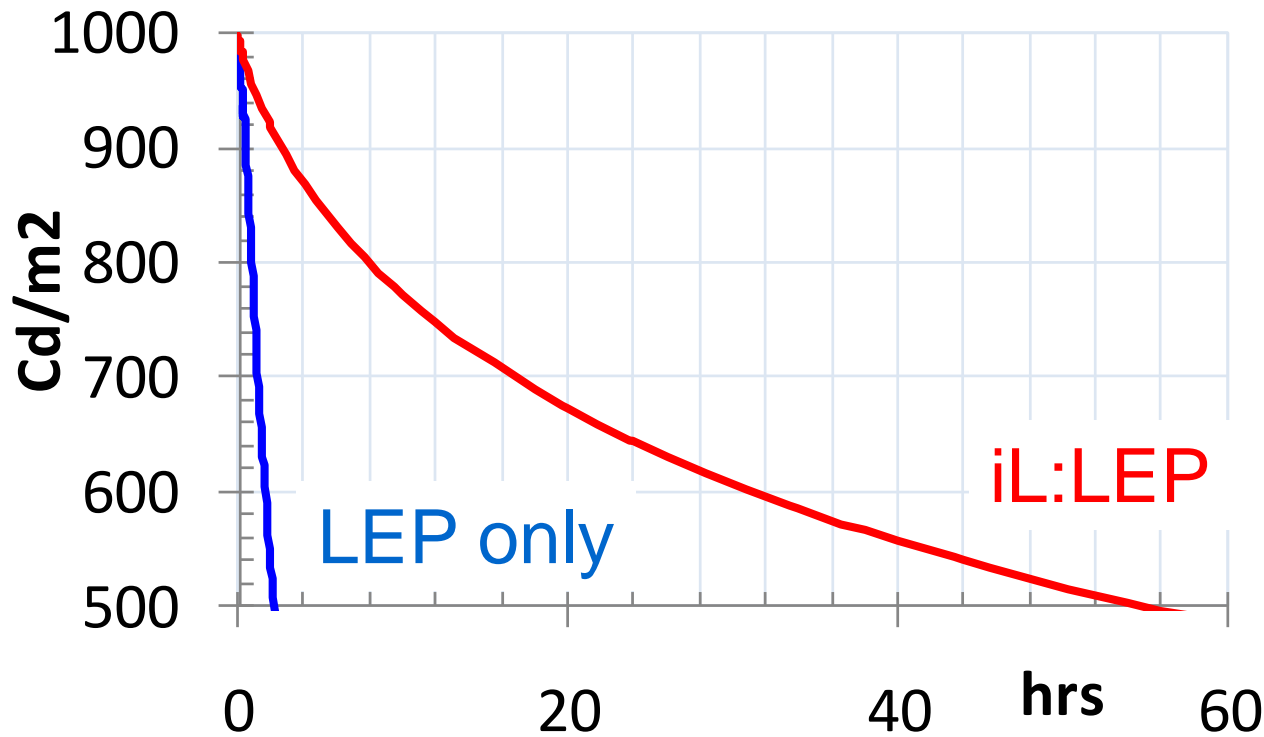
**LEP only vs iL:LEP**

**Model materials**

# Impact of iL

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iL:LEP = Model materials

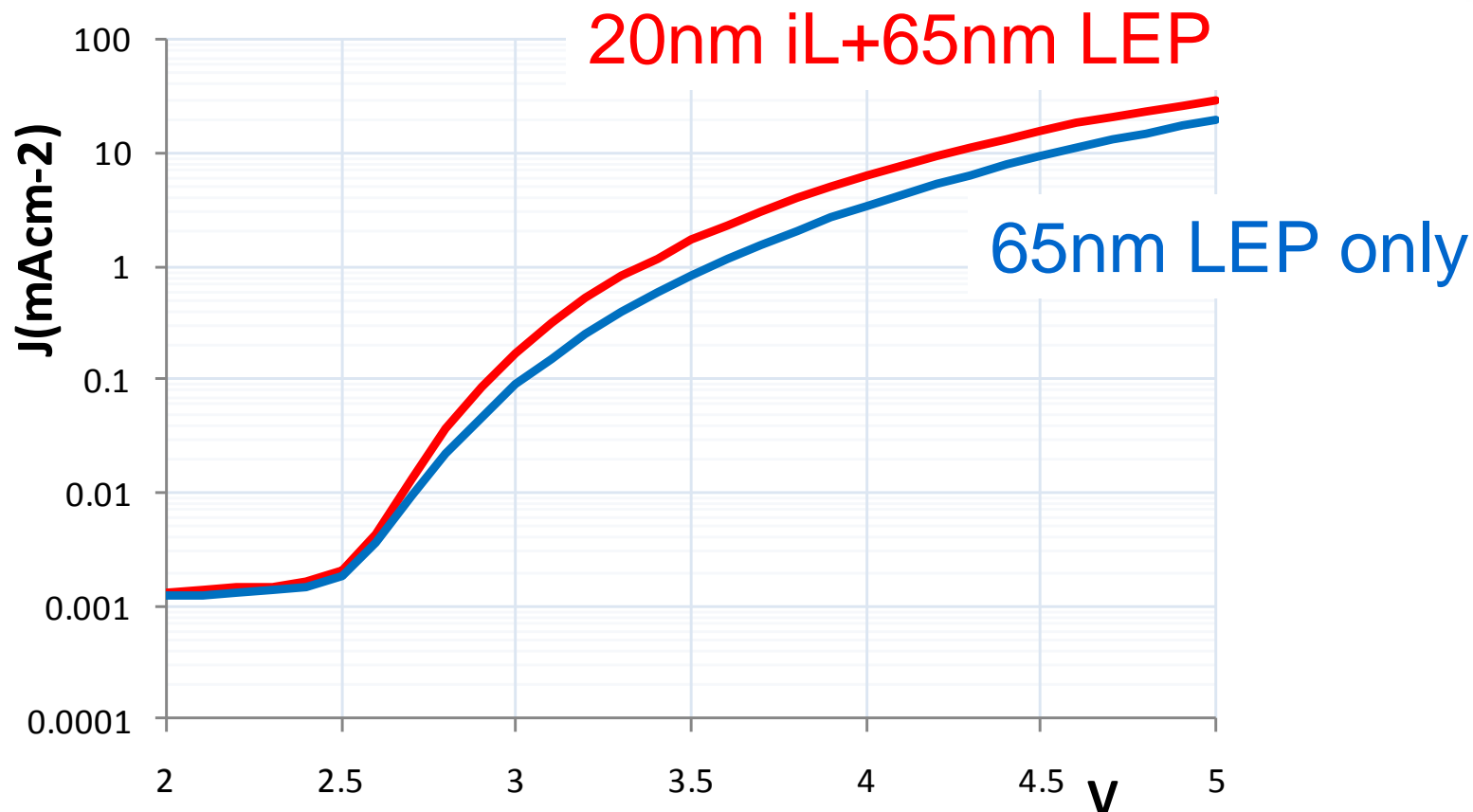


iL improves lifetime ×25

# Impact of iL

C|D|T

iL:LEP = Model materials

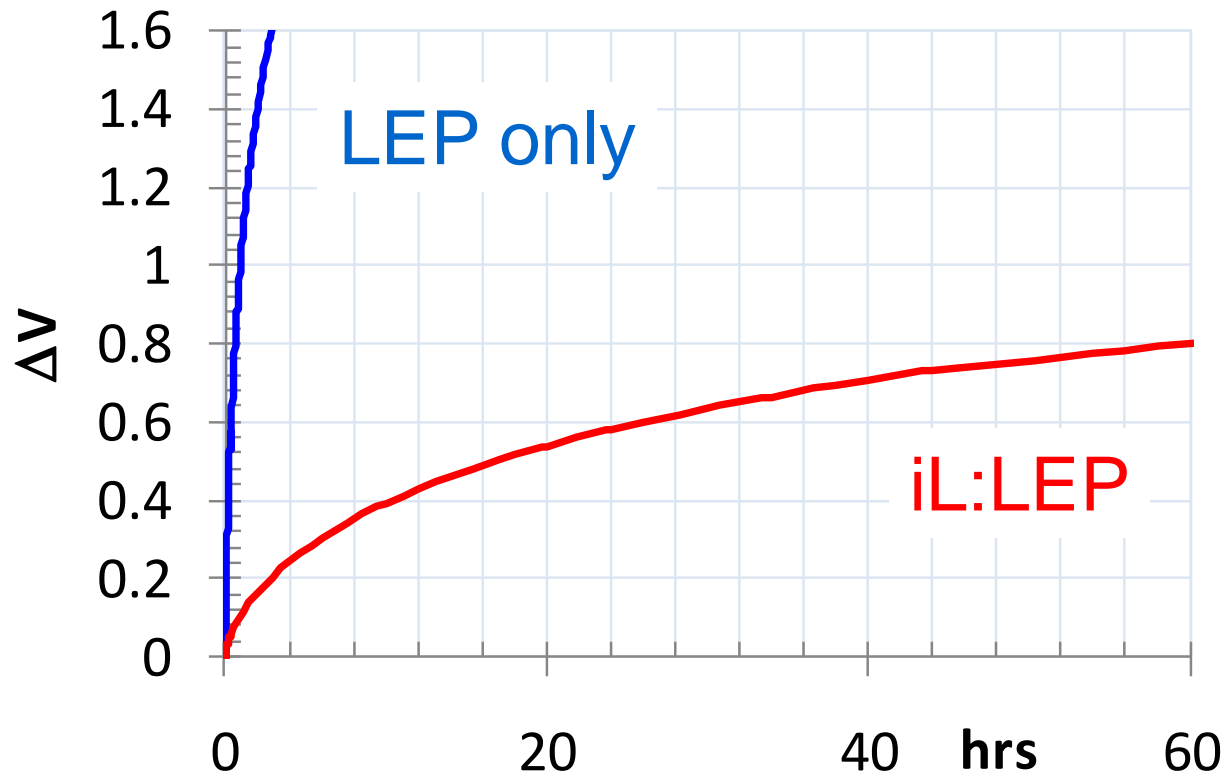


iL improves hole injection

# Impact of iL

C|D|T

iL:LEP = Model materials

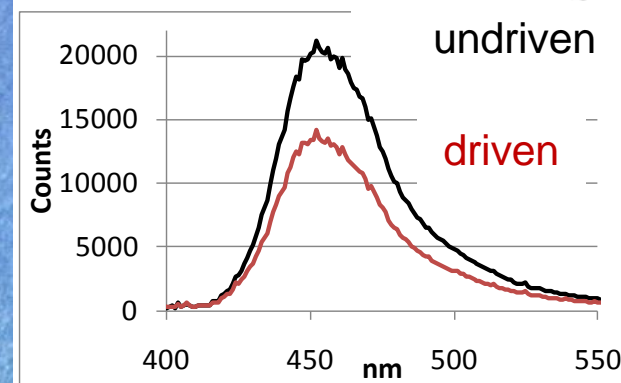
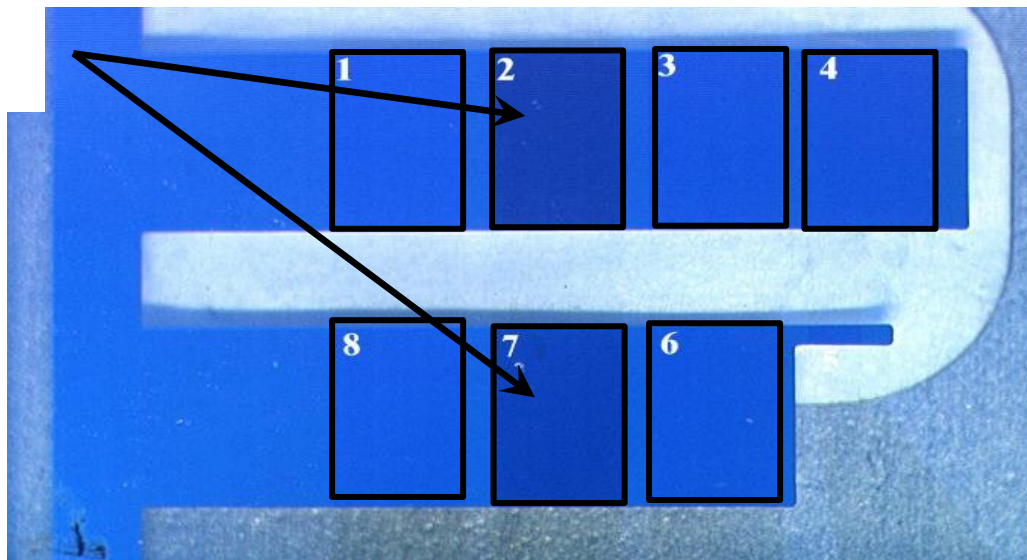


iL significantly reduces  $\Delta V/\Delta t$  and  $\Delta V$  at T50

## PL degradation

iL:LEP = Model materials

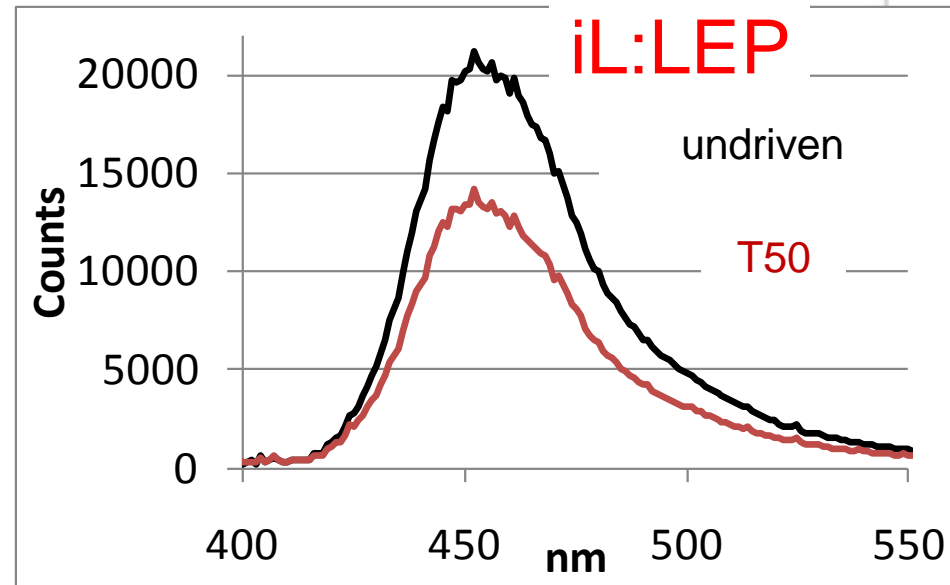
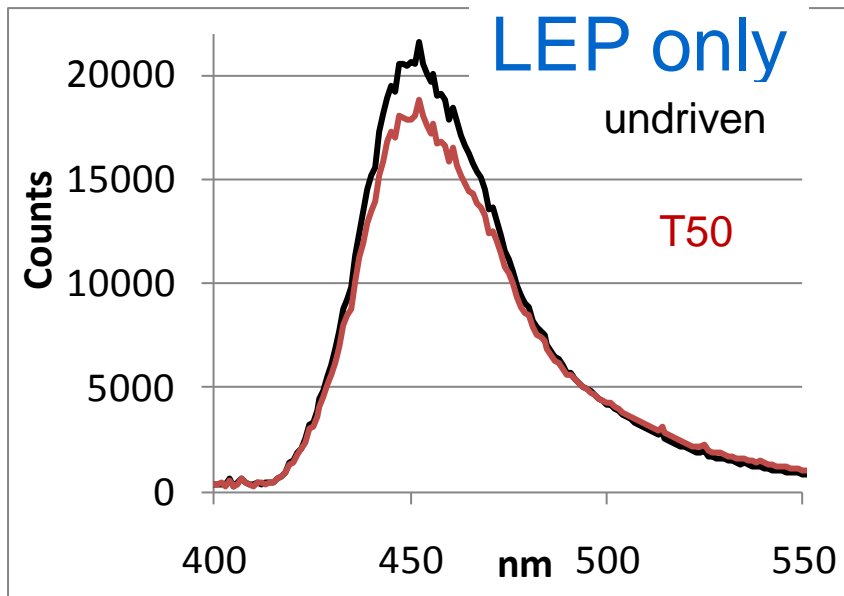
Driven pixels



- UV fluorescence can show clear evidence PLQE drop
- Note no greenshift in degraded spectrum

## Impact of iL

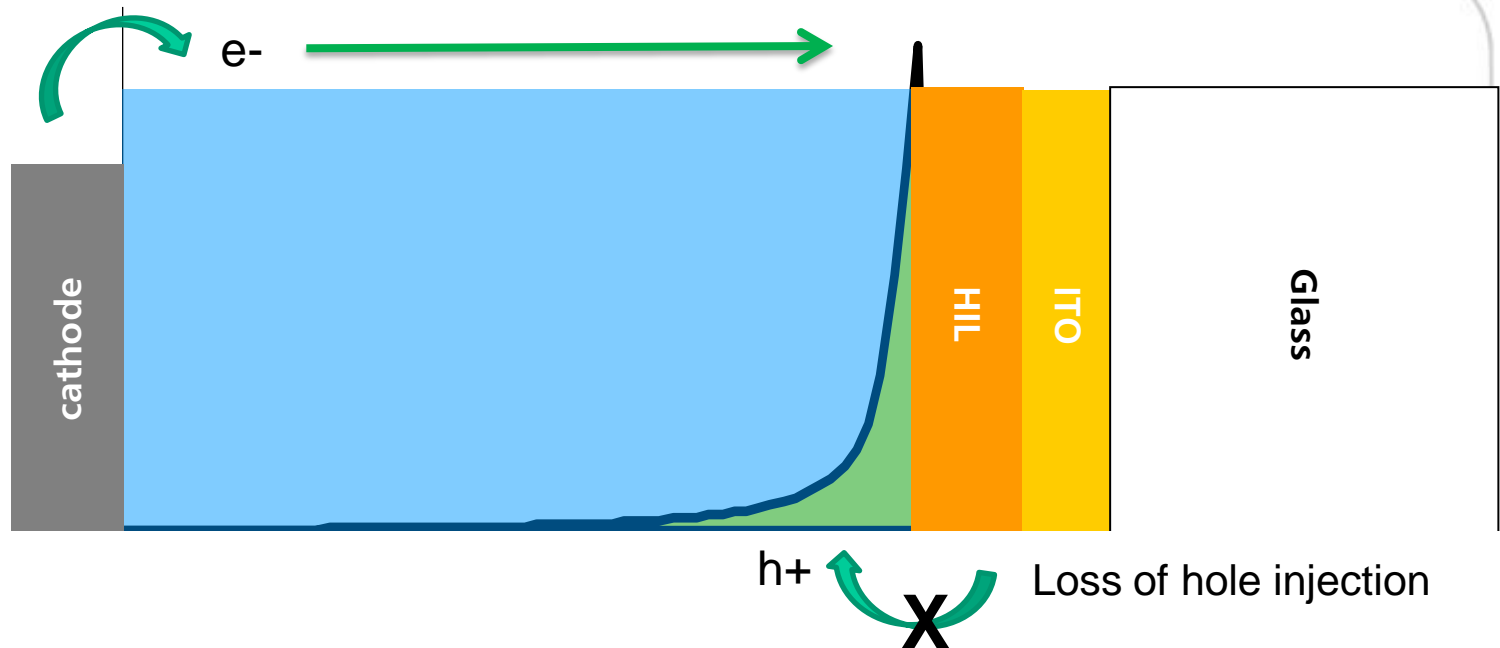
iL:LEP = Model materials



→ Relative importance of PL degradation increased with iL

# iL vs iL free device degradation

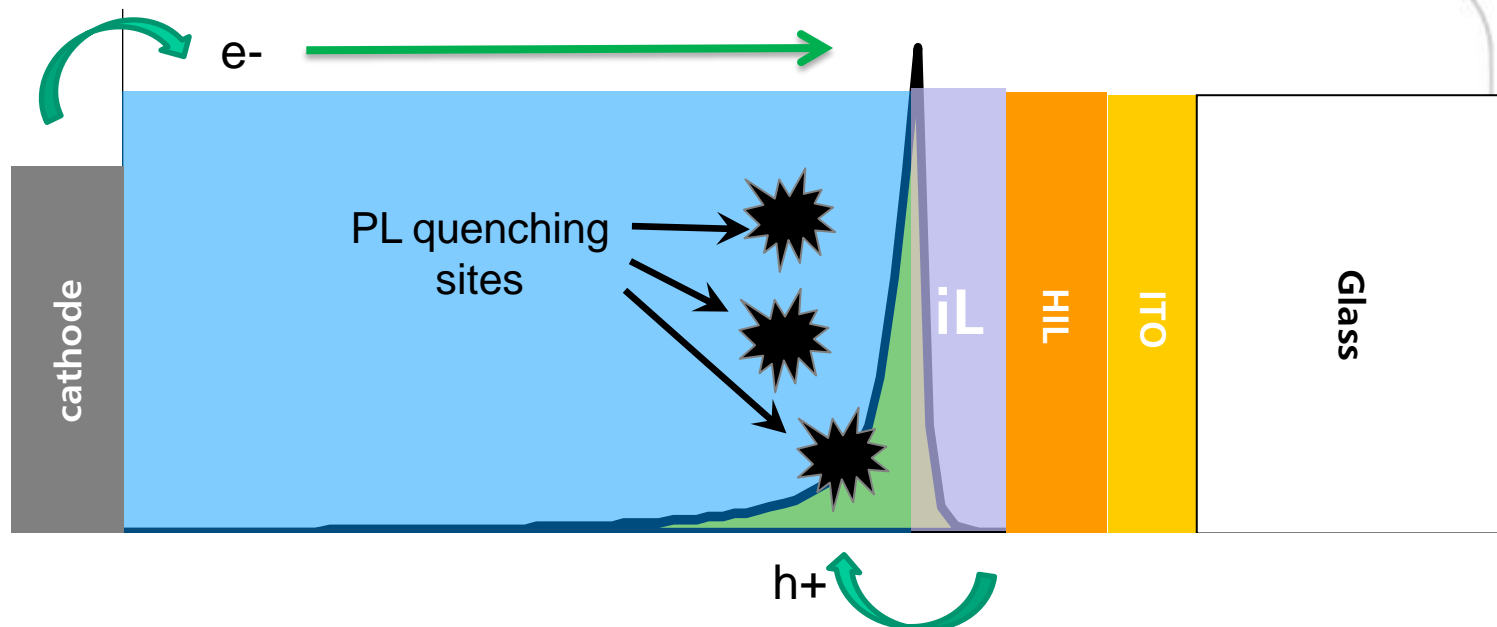
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- Understand in terms of 2 degradation mechanisms
- iL free device degradation dominated by hole injection failure

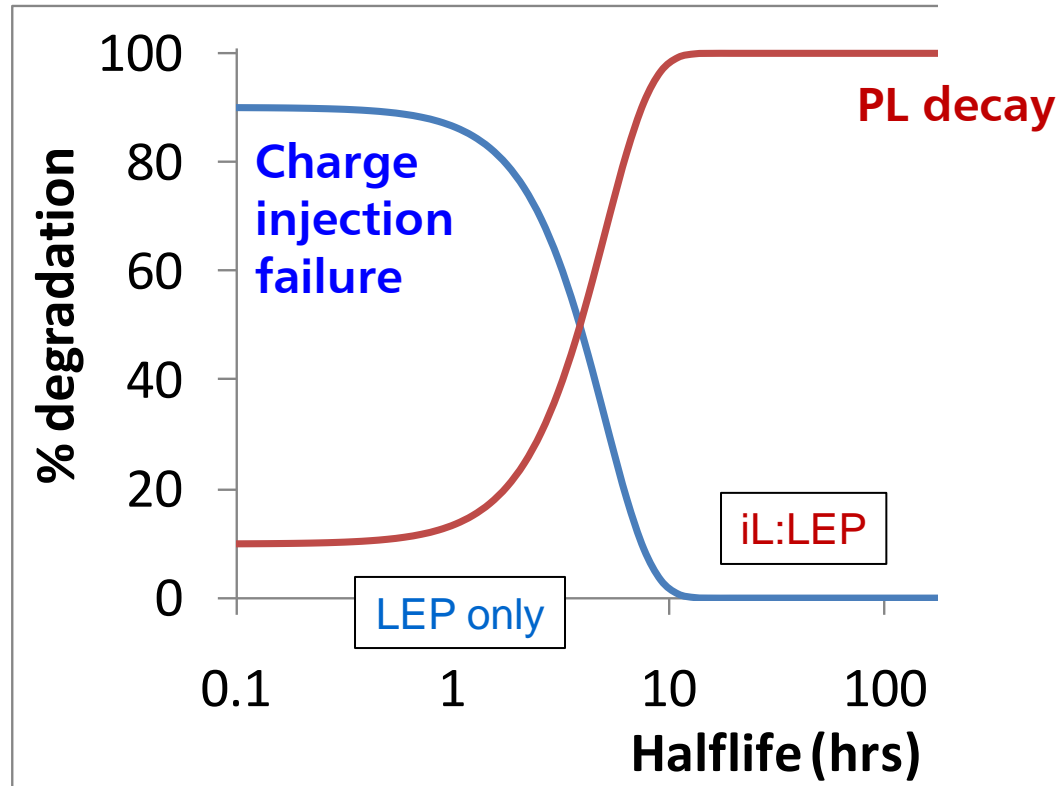
# iL vs iL free device degradation

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- Understand in terms of 2 degradation mechanisms
- iL free device degradation dominated by hole injection failure
- Stabilising charge injection failure allows us to look at intrinsic material stability, dominated by PL decay

# Summary : Degradation mechanisms C|D|T



## Case study 2

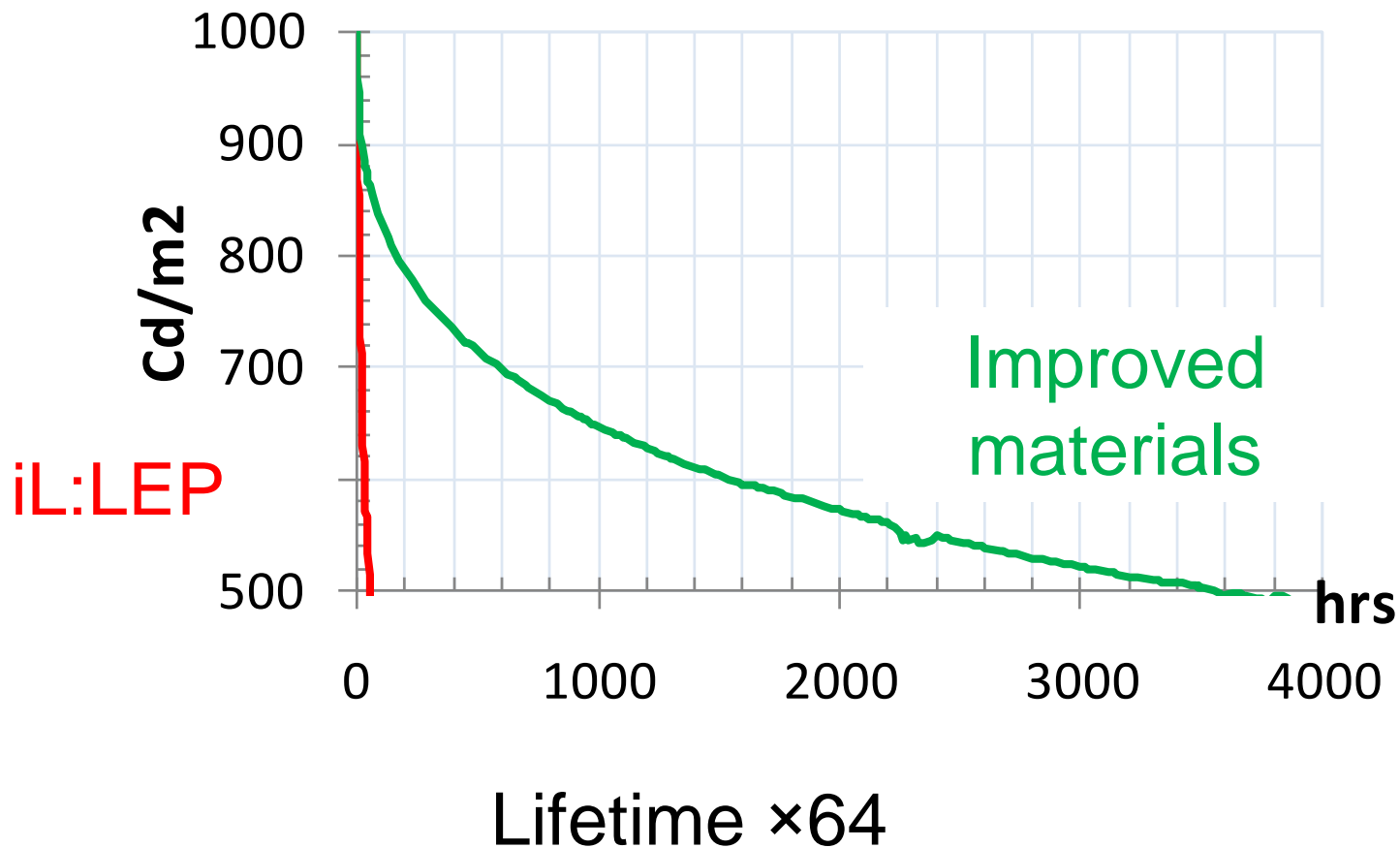
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# Model materials vs improved materials

## iL:LEP device structure

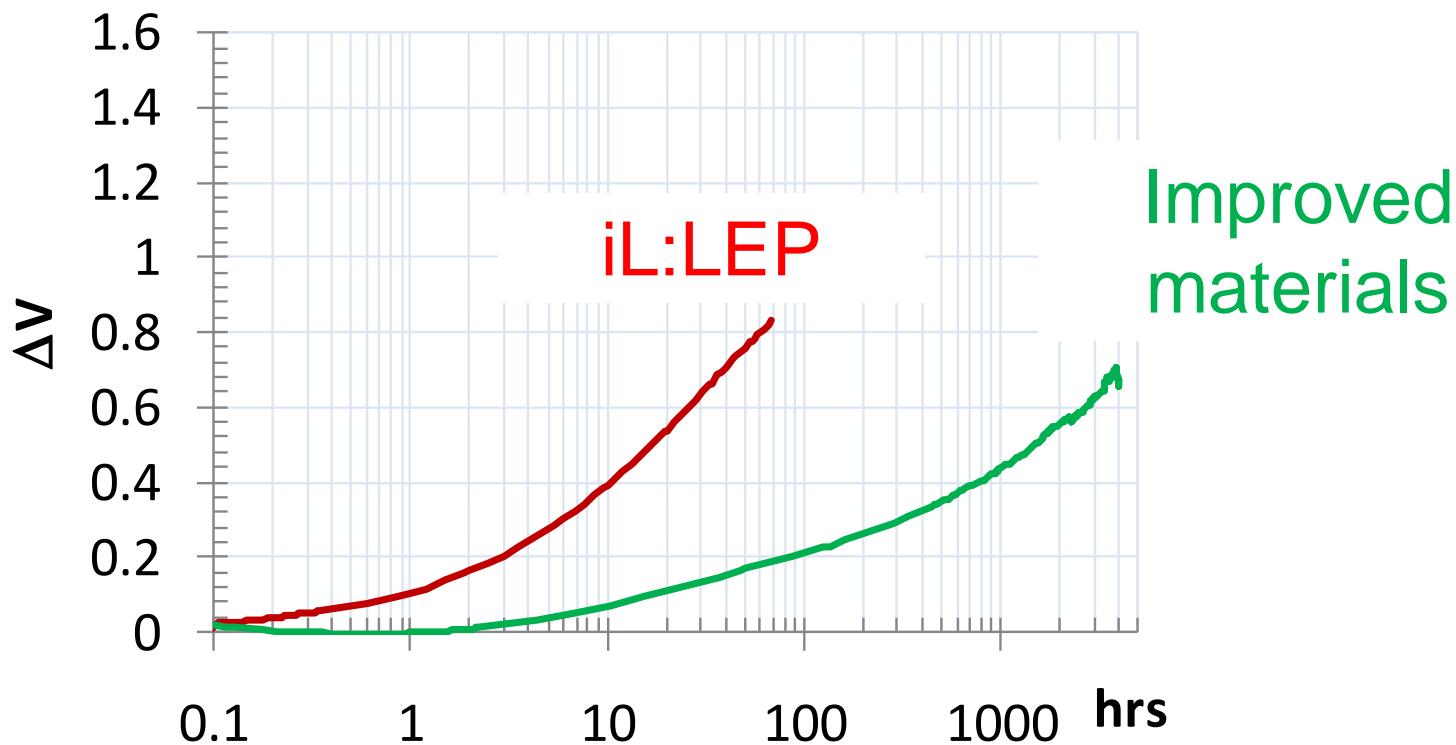
# Impact of improved materials

C | D | T



# Impact of improved materials

C | D | T

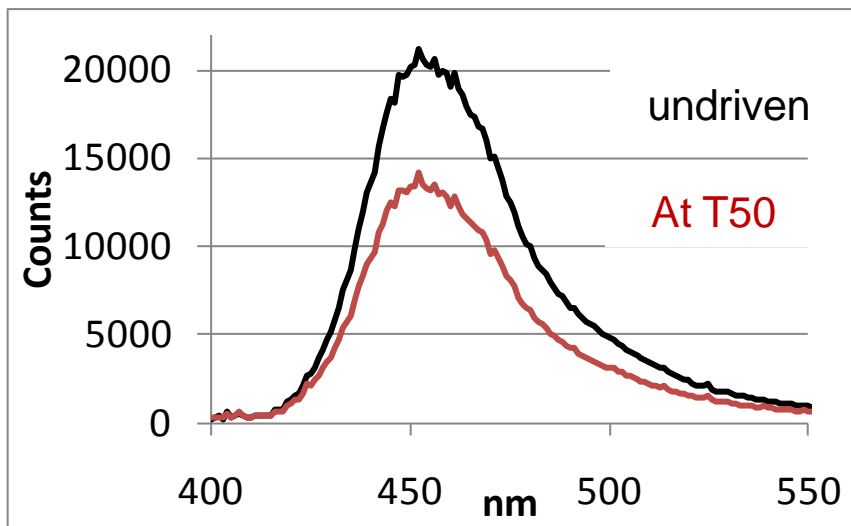


$\Delta V/\Delta t$  improved, but  $\Delta V$  at halflife similar.

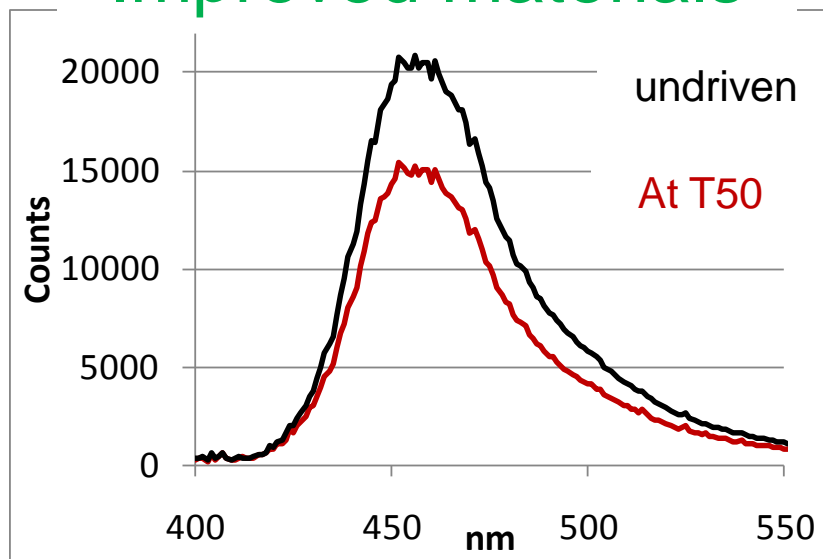
# Impact of improved materials

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iL:LEP



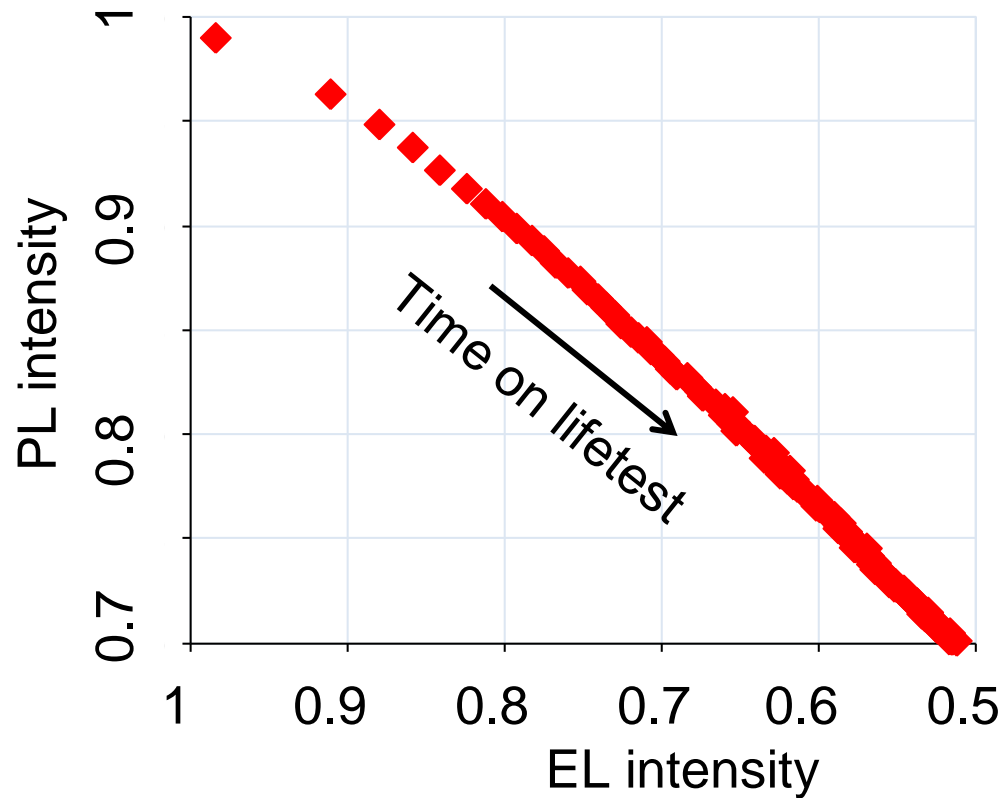
Improved materials



PL drop similar (~30%) over lifetime

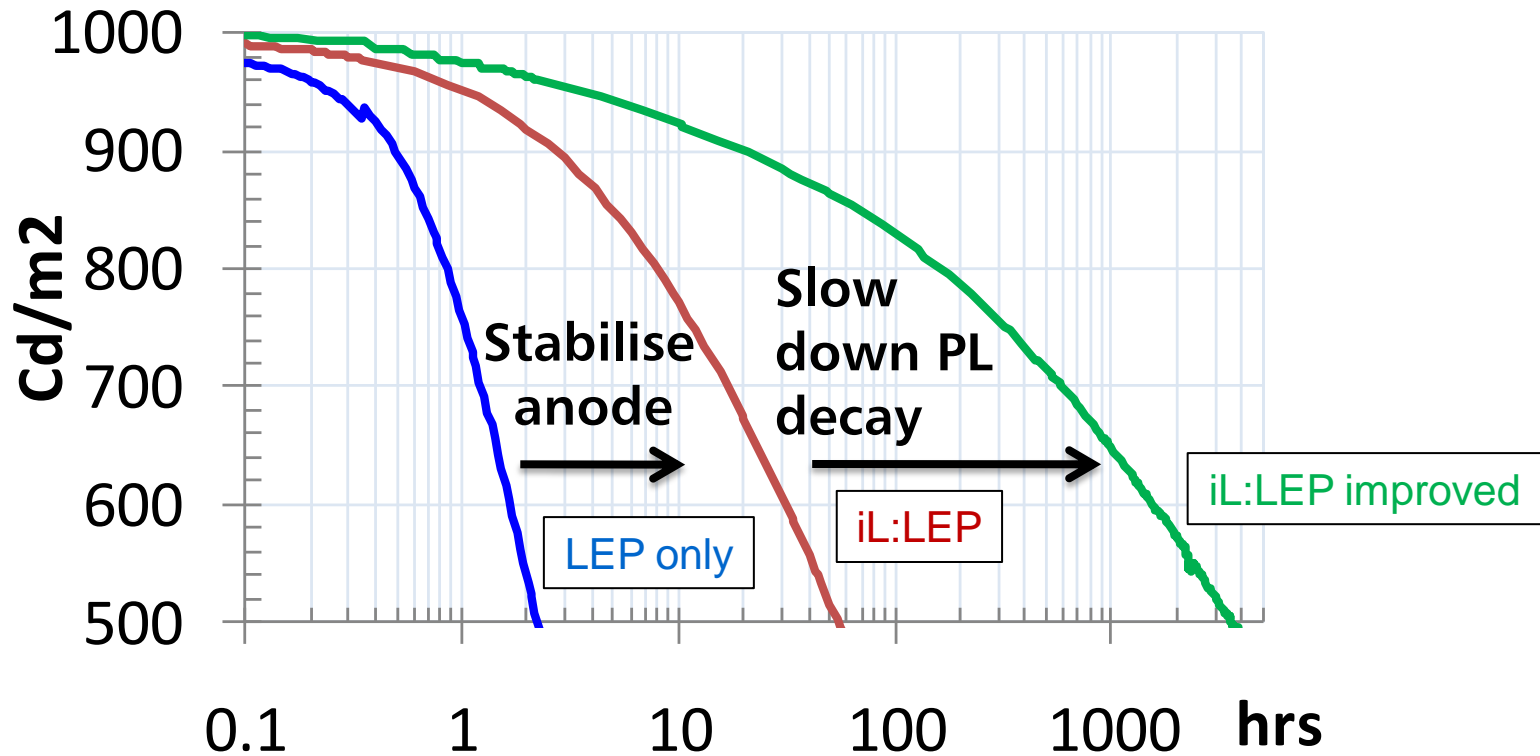
# EL vs PL decay

C|D|T



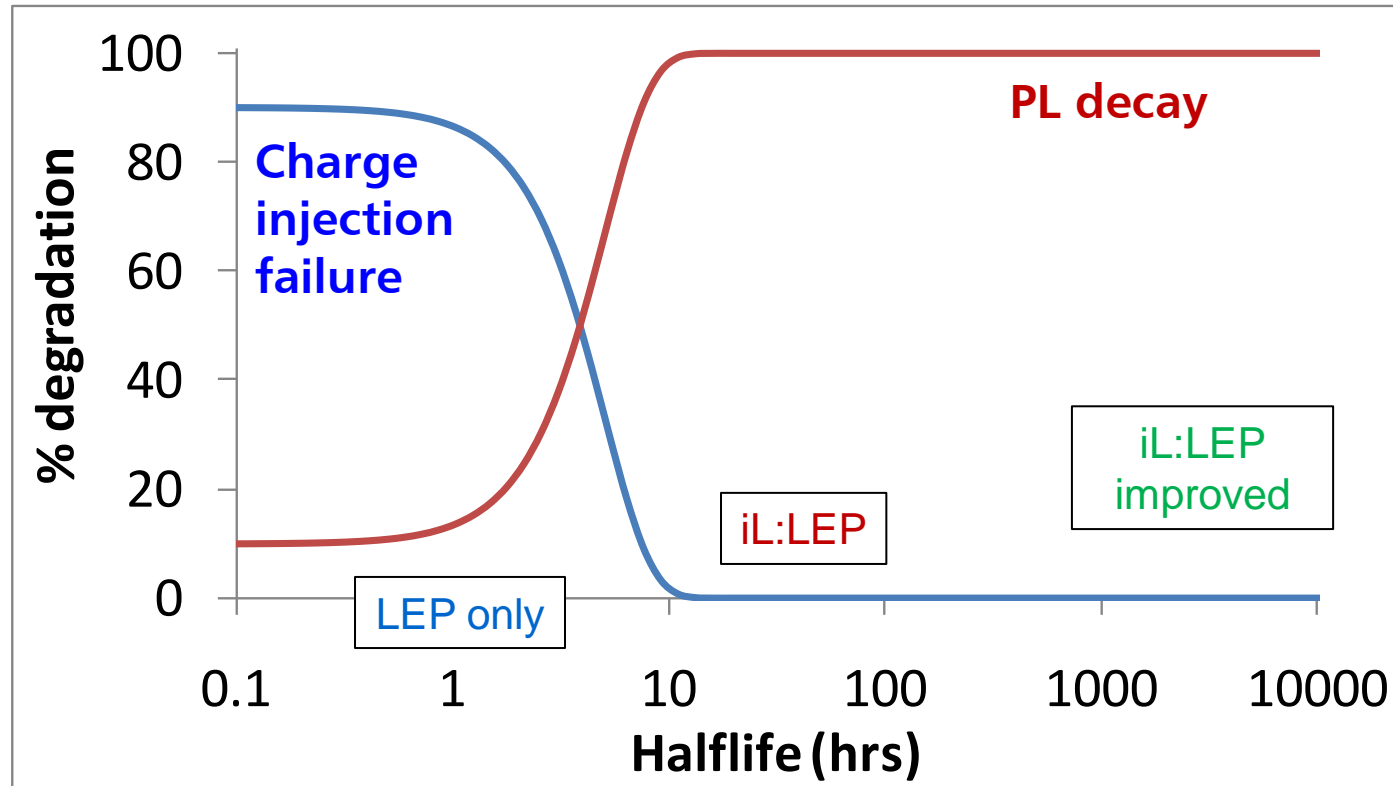
- 30% drop in PL for 50% drop in EL
- Narrow RZ suggests that PL drop might explain all of EL drop
- PL decay dominates degradation in model and improved materials

# Summary : Degradation mechanisms C|D|T



- Stabilising injection allows us to probe intrinsic material stability
- Slowing down PL decay rate can give dramatic improvements in T50

# Summary : Degradation mechanisms C|D|T



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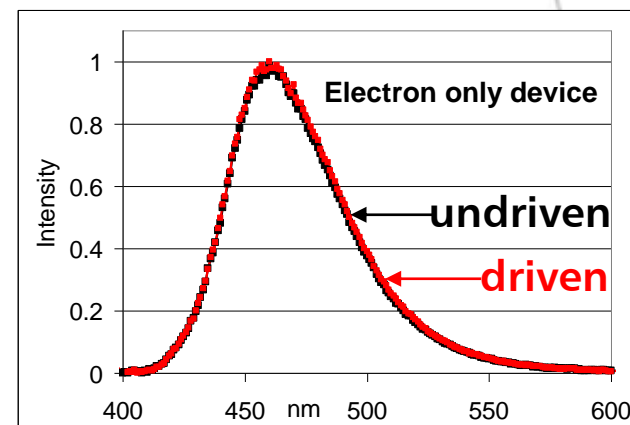
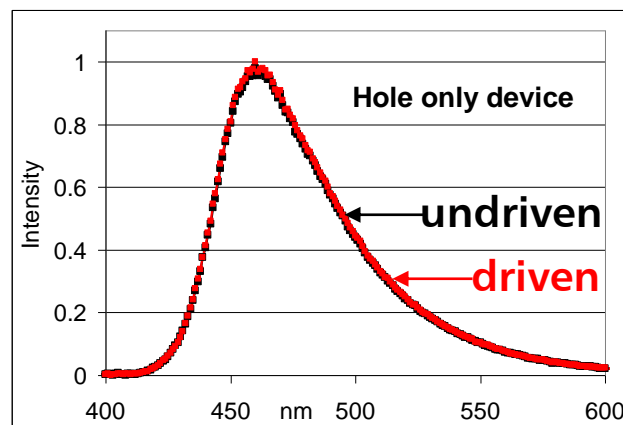
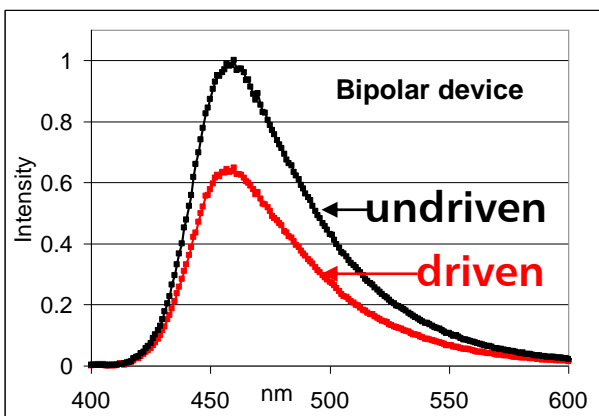
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- PL decay

## PL decay analysis

- What generates quench sites
- Properties of degraded material

# Cause of PL decay

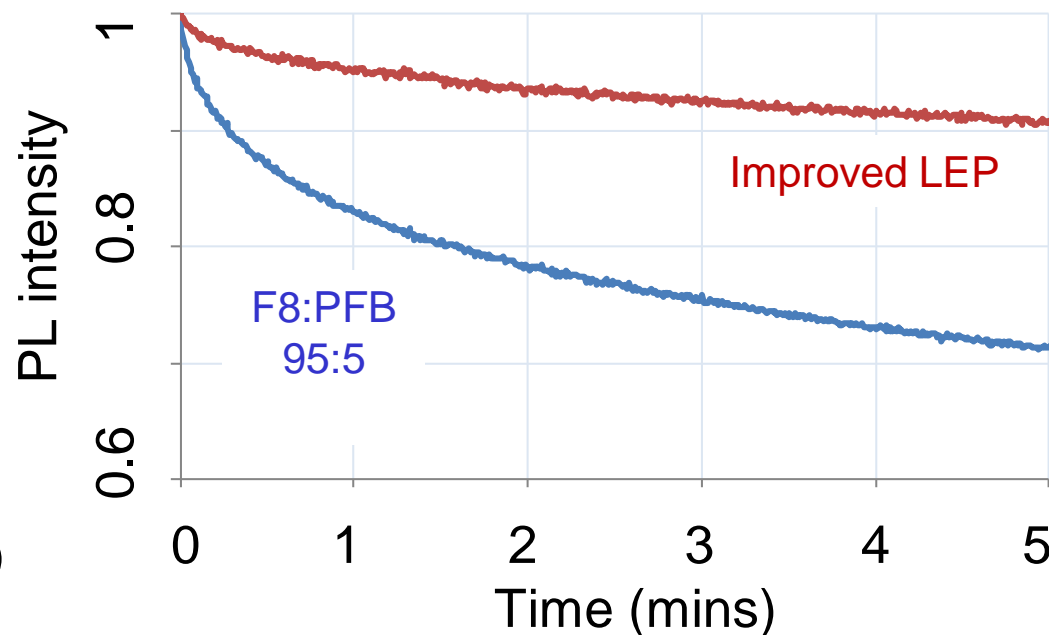
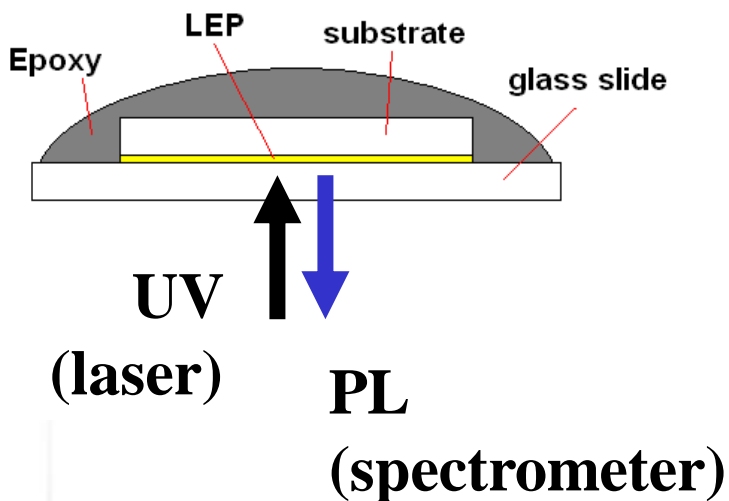
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→ Charge fluence alone does not generate PL quenching sites

# Cause of PL decay

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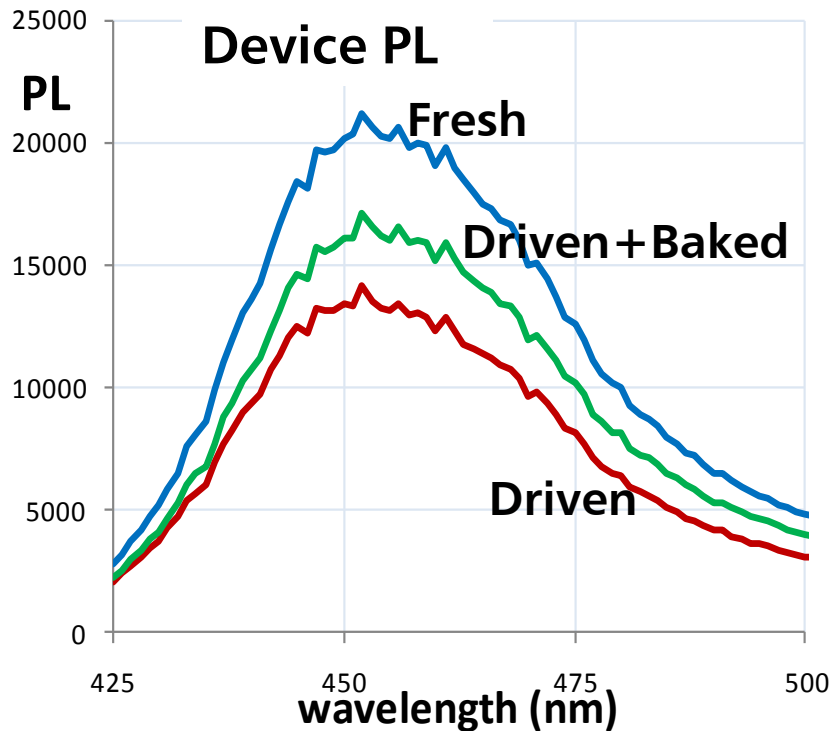


- UV generated excitons can generate PL quenching sites
- Improved LEP materials are more stable to excitons
- Excitons cause degradation

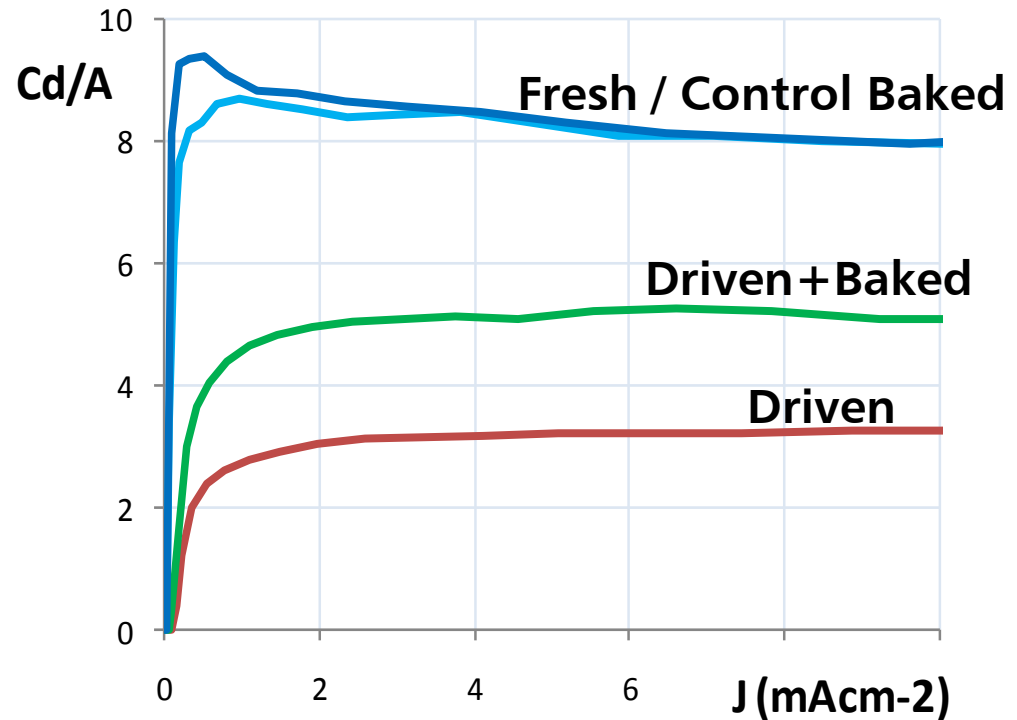
# Recovery of PL decay

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iL:LEP = Model materials



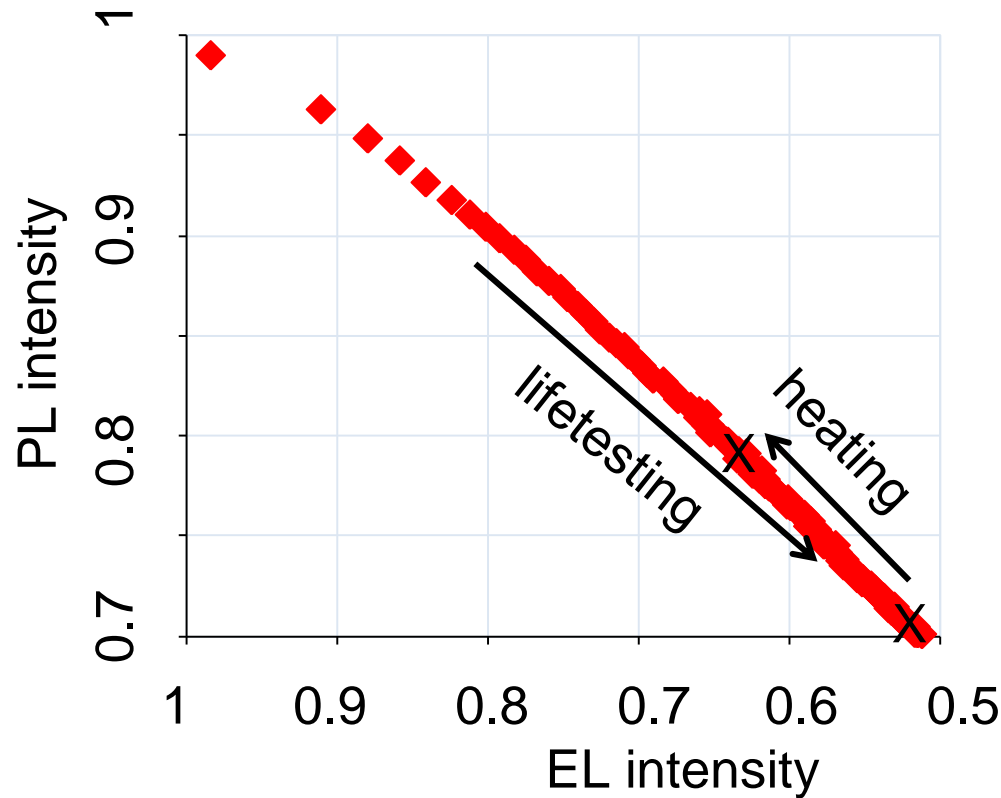
Device EL



- PL decay can be split into 'permanent' and 'recoverable' components
- ~40% of EL and PL decay at T50 can be recovered by baking!!

# EL vs PL decay

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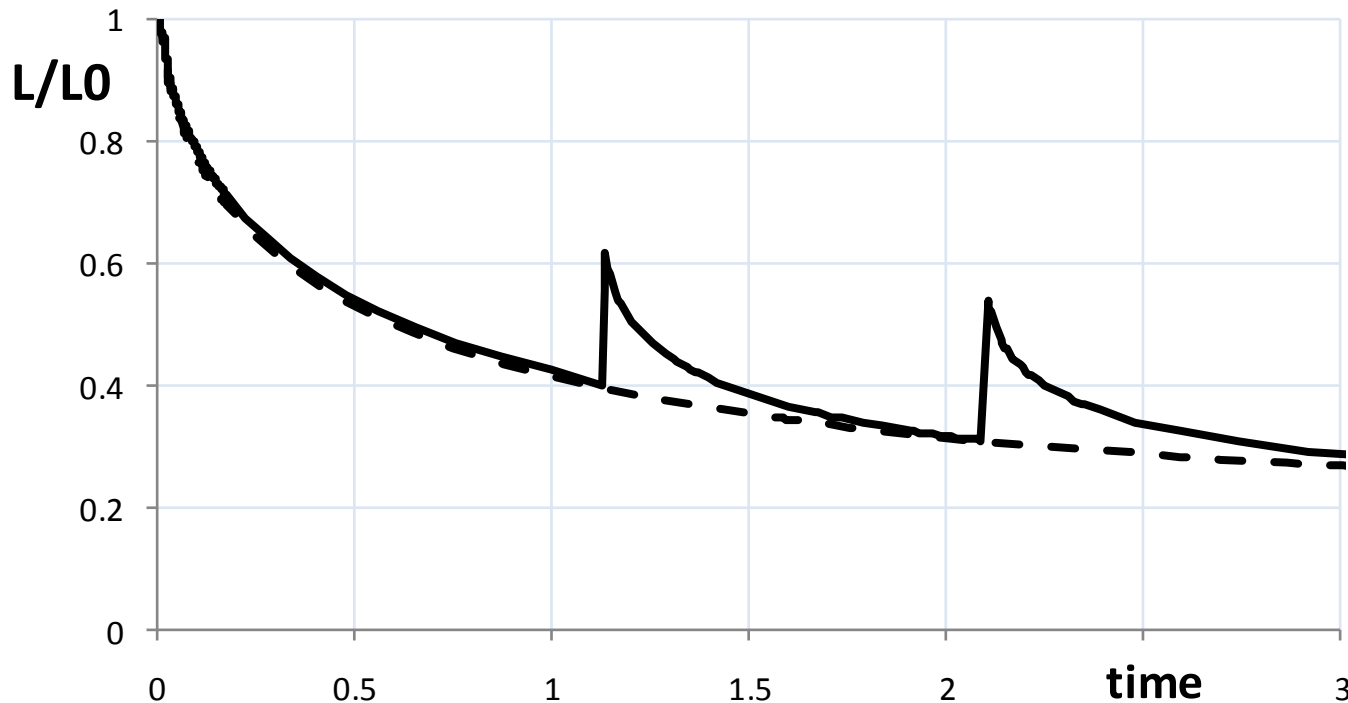


- Baking the device recovers the PL and EL
- Consistent with all of the EL drop being explained by PL drop
- Improved materials set give more PL recovery

# Reversibility of EL decay

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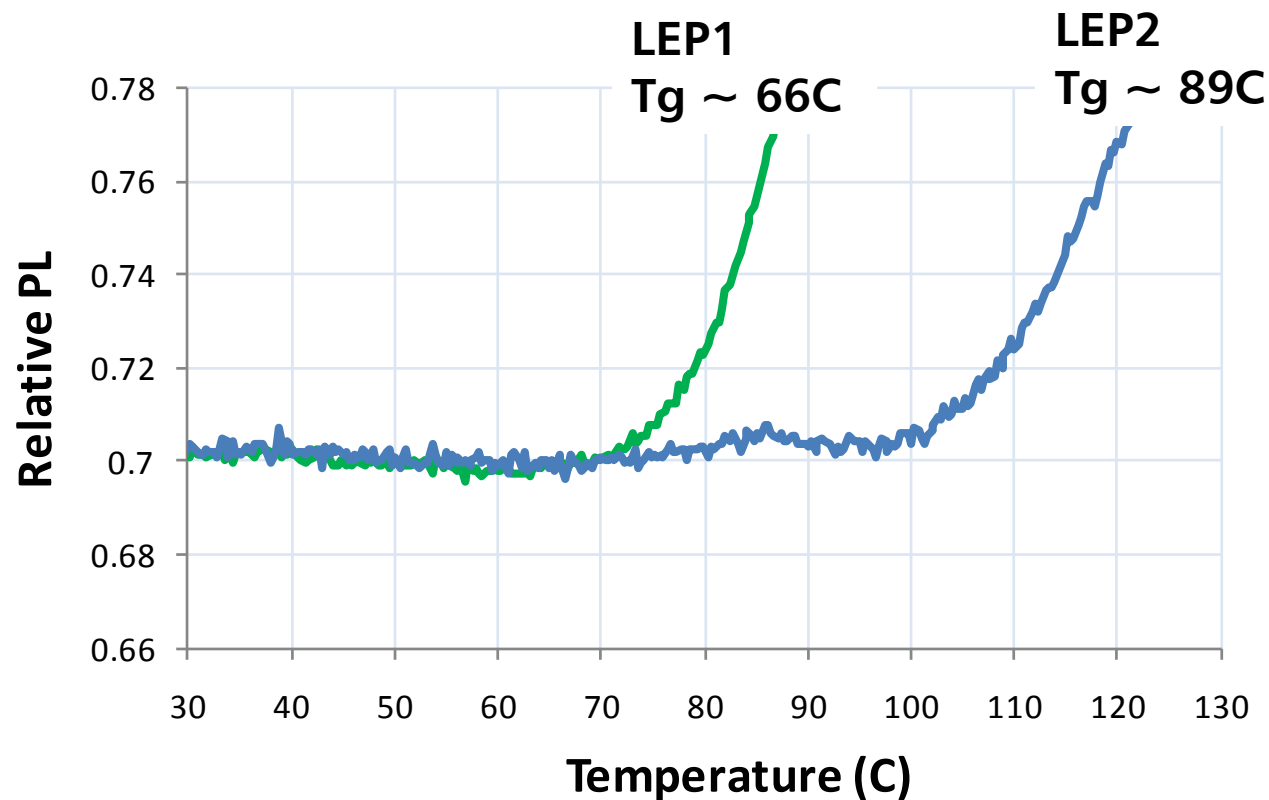
iL:LEP = Model materials



- In this model system, permanent component dominates
- Recoverable component of decay is truly recoverable – thus component of the degradation can really be ‘healed’

# Tg dependence of PL recovery

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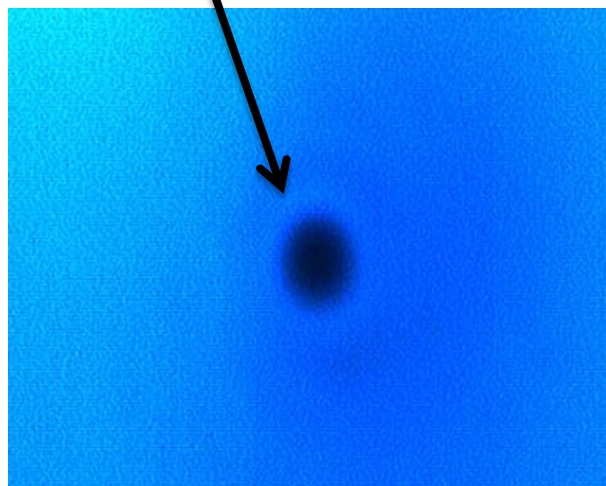
Threshold / activation temperature for PL recovery is the LEP Tg

# PL recovery in UV degraded films

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iL:LEP = improved materials

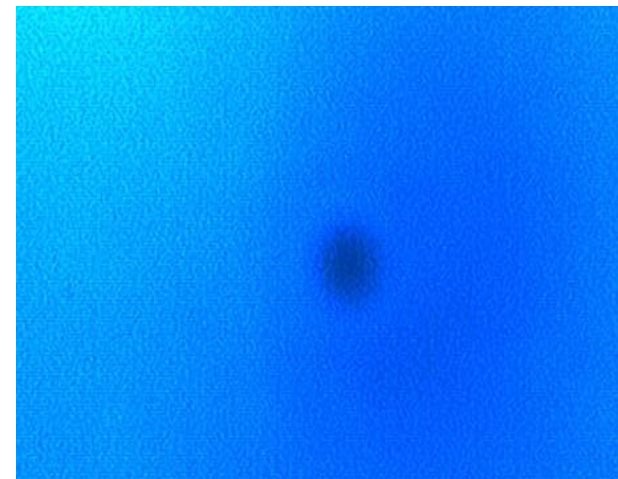
PL degraded area  
from UV laser  
illumination



Bake  
Above  
T<sub>g</sub>



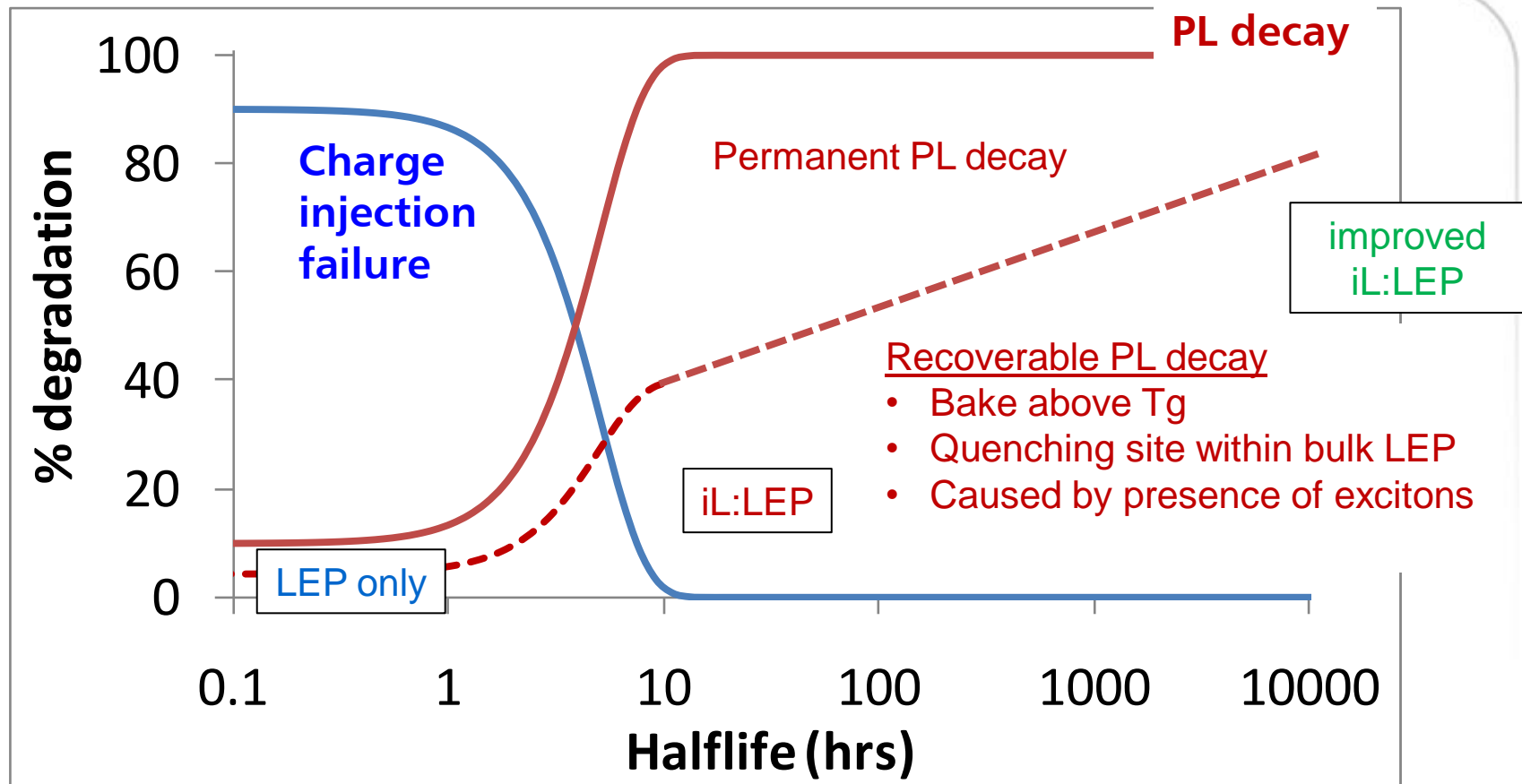
Significant recovery of  
PL in degraded area



Significant recoverable PL is also observed in UV degraded films

# Summary: P-OLED stability

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- Understanding the reversible PL decay is key to improving P-OLED lifetimes
- Model materials set show similar but vastly accelerated degradation mechanism
- Optical excitation provides a simple model for understanding fundamental mechanisms